

General Description

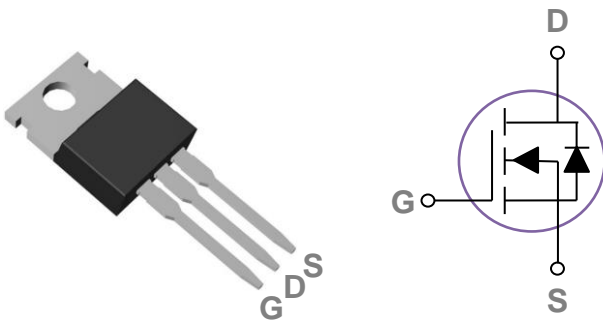
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	R _{DS(ON)}	I _D
80V	2.6mΩ	200A

Features

- 80V,200A, R_{DS(ON)} =2.6mΩ@V_{GS} = 10V
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

TO220 Pin Configuration



Applications

- Networking
- Load Switch
- LED applications

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	80	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current – Continuous (T _C =25°C)	200	A
	Drain Current – Continuous (T _C =100°C)	126	A
I _{DM}	Drain Current – Pulsed ¹	800	A
EAS	Single Pulse Avalanche Energy ²	1280	mJ
IAS	Single Pulse Avalanche Current ²	160	A
P _D	Power Dissipation (T _C =25°C)	208	W
	Power Dissipation – Derate above 25°C	1.66	W/°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction to ambient	---	62	°C/W
R _{θJC}	Thermal Resistance Junction to Case	---	0.6	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	80	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.05	---	V/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =64V, V _{GS} =0V, T _J =125°C	---	---	10	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A	---	2	2.6	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.5	2.2	3.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-5	---	mV/°C
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =3A	---	18	---	S

Dynamic and switching Characteristics

Q _g	Total Gate Charge ^{3,4}	V _{DS} =40V, V _{GS} =10V, I _D =10A	---	247	360	nC
Q _{gs}	Gate-Source Charge ^{3,4}		---	63.5	125	
Q _{gd}	Gate-Drain Charge ^{3,4}		---	56	110	
T _{d(on)}	Turn-On Delay Time ^{3,4}	V _{DD} =40V, V _{GS} =10V, R _G =10Ω I _D =10A	---	71	140	ns
T _r	Rise Time ^{3,4}		---	103	200	
T _{d(off)}	Turn-Off Delay Time ^{3,4}		---	291	580	
T _f	Fall Time ^{3,4}		---	170	340	
C _{iss}	Input Capacitance	V _{DS} =30V, V _{GS} =0V, F=1MHz	---	15010	23000	pF
C _{oss}	Output Capacitance		---	772	1200	
C _{rss}	Reverse Transfer Capacitance		---	81	160	
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	---	1.8	3.6	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	200	A
I _{SM}	Pulsed Source Current		---	---	400	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1	V
t _{rr}	Reverse Recovery Time	V _{GS} =0V, I _S =20A, di/dt=100A/μs	---	54	---	ns
Q _{rr}	Reverse Recovery Charge	T _J =25°C	---	78	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=50V, V_{GS}=10V, L=0.1mH, I_{AS}=160A., Starting T_J=25°C
3. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.

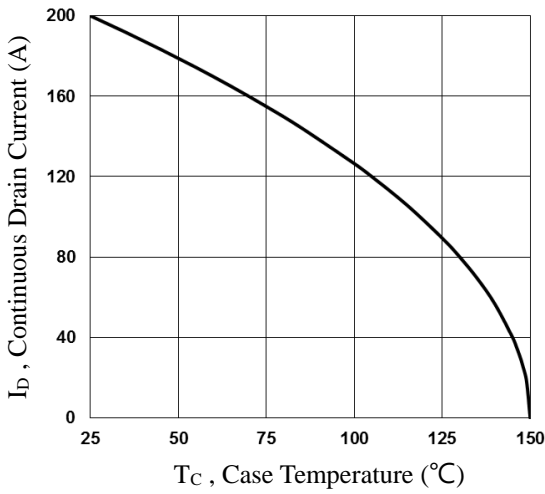


Fig.1 Continuous Drain Current vs. T_c

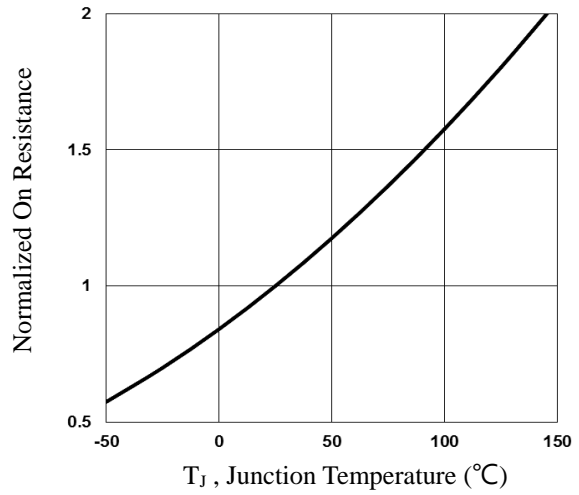


Fig.2 Normalized $R_{DS(on)}$ vs. T_j

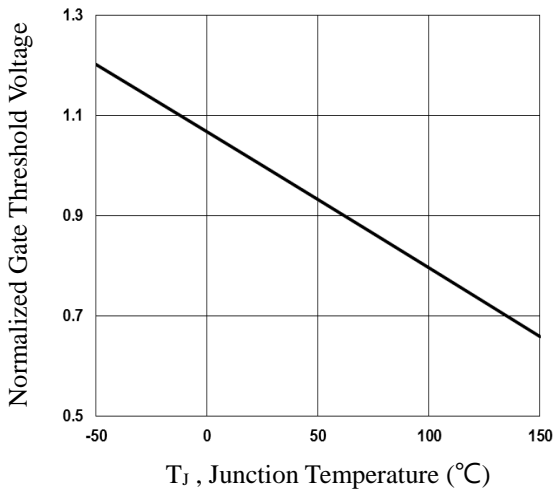


Fig.3 Normalized V_{th} vs. T_j

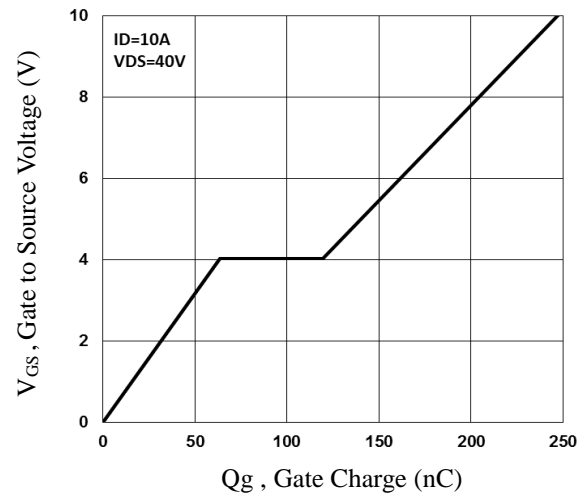


Fig.4 Gate Charge Characteristics

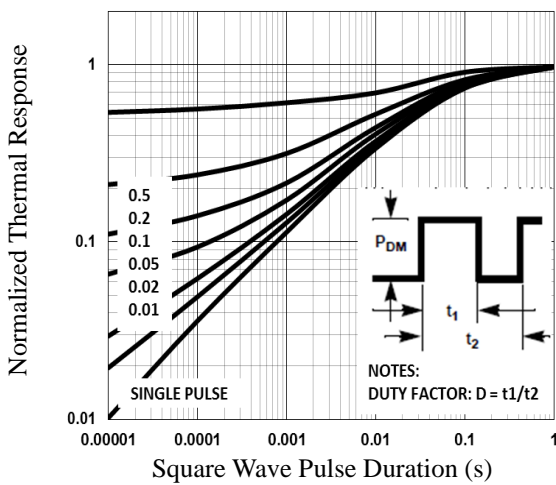


Fig.5 Normalized Transient Impedance

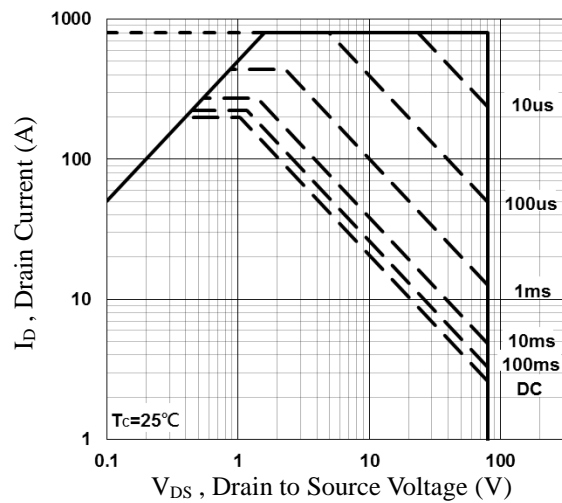


Fig.6 Maximum Safe Operation Area

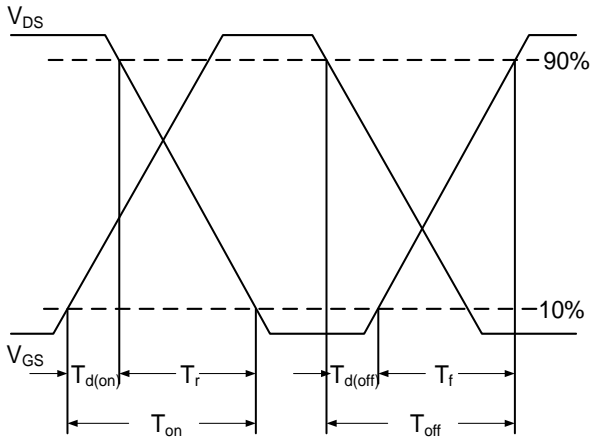
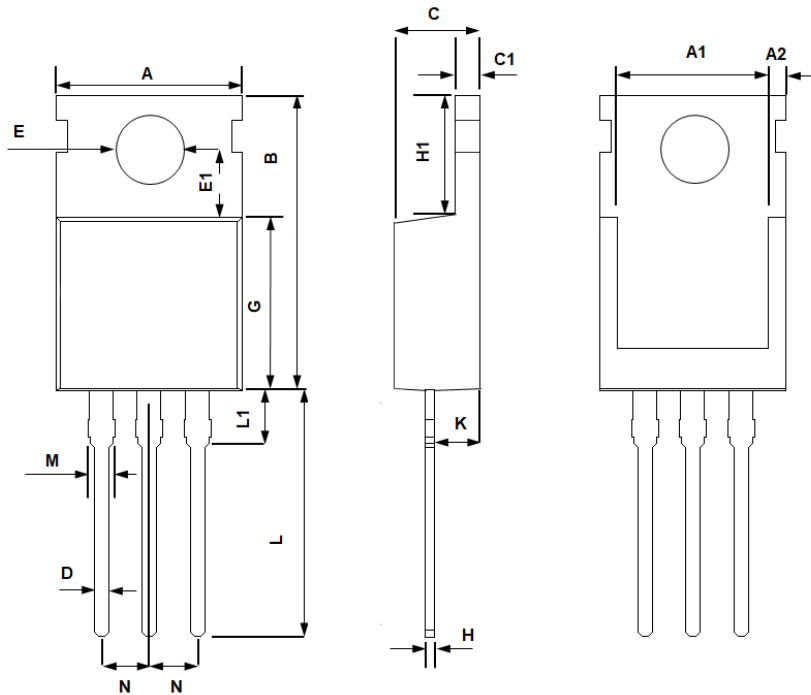


Fig.7 Switching Time Waveform



Fig.8 Gate Charge Waveform

TO220 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	10.400	9.700	0.409	0.382
A1	8.900	7.400	0.350	0.291
A2	1.400	0.800	0.055	0.031
B	16.500	14.500	0.650	0.571
C	4.750	4.200	0.187	0.165
C1	1.500	1.100	0.059	0.043
D	1.000	0.600	0.039	0.024
E	4.000	3.300	0.157	0.130
E1	3.800	3.400	0.150	0.134
G	9.400	8.400	0.370	0.331
H	0.600	0.200	0.024	0.008
H1	6.850	6.200	0.270	0.244
K	2.850	2.100	0.112	0.083
L	14.000	12.500	0.551	0.492
L1	4.000	2.700	0.157	0.106
M	1.750	1.100	0.069	0.043
N	2.640	2.440	0.104	0.096